

HiPerFET™ Power MOSFETs

IXFK 90 N 20
IXFN 100 N 20
IXFN 106 N 20

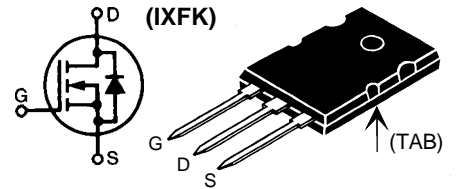
V_{DSS}	I_{D25}	$R_{DS(on)}$
200 V	90 A	23 mΩ
200 V	100 A	23 mΩ
200 V	106 A	20 mΩ

N-Channel Enhancement Mode
Avalanche Rated, High dv/dt, Low t_{rr}

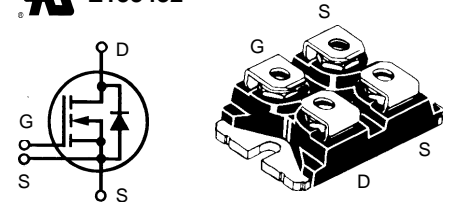
$t_{rr} \leq 200$ ns

Symbol	Test Conditions	Maximum Ratings		
		IXFK	IXFN	IXFN
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	90N20 200	100N20 200	106N20 200 V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1$ MΩ	200	200	200 V
V_{GS}	Continuous	±20	±20	20 V
V_{GSM}	Transient	±30	±30	20 V
I_{D25}	$T_C = 25^\circ\text{C}$, Chip capability	90 ①	100	106 A
I_{D80}	$T_C = 80^\circ\text{C}$, limited by external leads	76	-	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	360	400	424 A
I_{AR}	$T_C = 25^\circ\text{C}$	50	50	A
E_{AR}	$T_C = 25^\circ\text{C}$	30	30	30 mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100$ A/μs, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2$ Ω	5	5	5 V/ns
P_D	$T_C = 25^\circ\text{C}$	500	520	W
T_J		-55 ... +150		°C
T_{JM}		150		°C
T_{stg}		-55 ... +150		°C
T_L	1.6 mm (0.063 in) from case for 10 s	300	-	°C
V_{ISOL}	50/60 Hz, RMS $t = 1$ min $I_{ISOL} \leq 1$ mA $t = 1$ s	-	2500	V~
		-	3000	V~
M_d	Mounting torque	0.9/6	1.5/13	Nm/lb.in.
	Terminal connection torque	-	1.5/13	Nm/lb.in.
Weight		10	30	g

TO-264 AA



miniBLOC, SOT-227 B (IXFN)
E153432



G = Gate
S = Source

D = Drain
TAB = Drain

Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Features

- International standard packages
- JEDEC TO-264 AA, epoxy meet UL94 V-0, flammability classification
- miniBLOC with Aluminium nitride isolation
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls
- Low voltage relays

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0$ V, $I_D = 1$ mA	200		V
$V_{GH(th)}$	$V_{DS} = V_{GS}$, $I_D = 8$ mA	2		V
I_{GSS}	$V_{GS} = \pm 20$ V _{DC} , $V_{DS} = 0$			±200 nA
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$, $T_J = 25^\circ\text{C}$ $V_{GS} = 0$ V, $T_J = 125^\circ\text{C}$			400 μA 2 mA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300$ μs, duty cycle $d \leq 2$ %			IXFK90N20 0.023 Ω IXFN100N20 0.023 Ω IXFN106N20 0.020 Ω

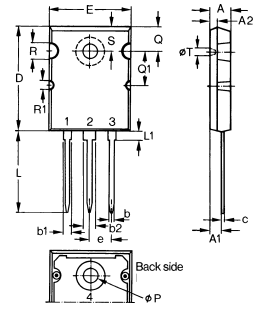
IXYS reserves the right to change limits, test conditions, and dimensions.

92804H (7/97)

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test		60	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		9000	pF
C_{oss}			1600	pF
C_{rss}			590	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\ \Omega$ (External),		30	ns
t_r			80	ns
$t_{d(off)}$			75	ns
t_f			30	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		380	nC
Q_{gs}			70	nC
Q_{gd}			190	nC
R_{thJC}	TO-264 AA		0.25	K/W
R_{thCK}	TO-264 AA		0.15	K/W
R_{thJC}	miniBLOC, SOT-227 B		0.24	K/W
R_{thCK}	miniBLOC, SOT-227 B		0.05	K/W

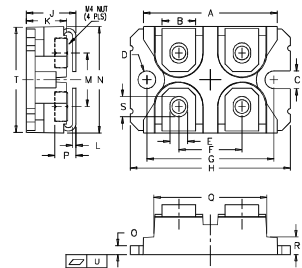
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			90 A IXFK90N20 IXFN100N20 IXFN106N20
I_{SM}	Repetitive; pulse width limited by T_{JM}			360 A IXFK90N20 424 A IXFN100N20 IXFN106N20
V_{SD}	$I_F = 100\text{ A}, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = 50\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		3	200 ns
Q_{RM}			38	μC
I_{RM}				A

TO-264 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46	BSC	.215	BSC
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

Fig. 1 Output Characteristics

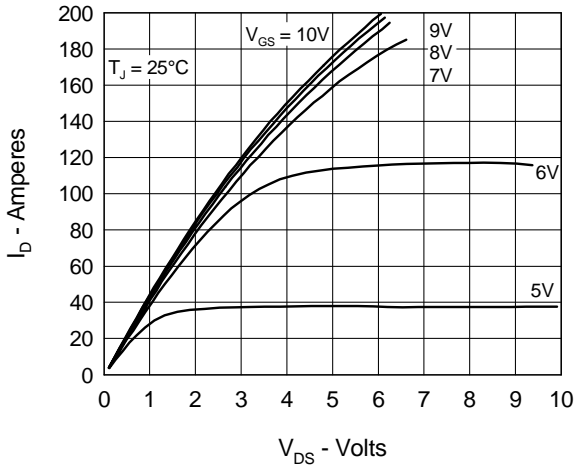


Fig. 2 Input Admittance

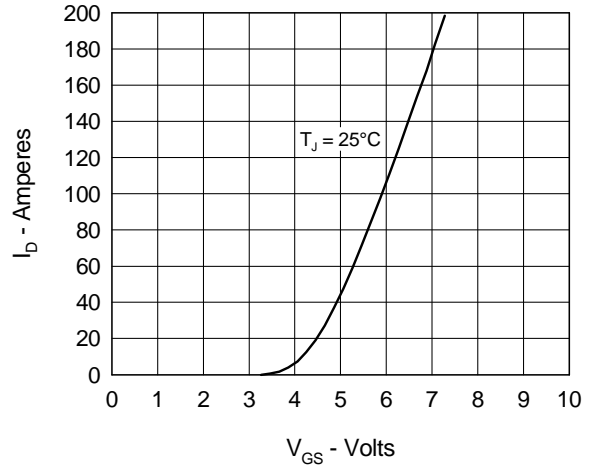


Fig. 3 $R_{DS(on)}$ vs. Drain Current

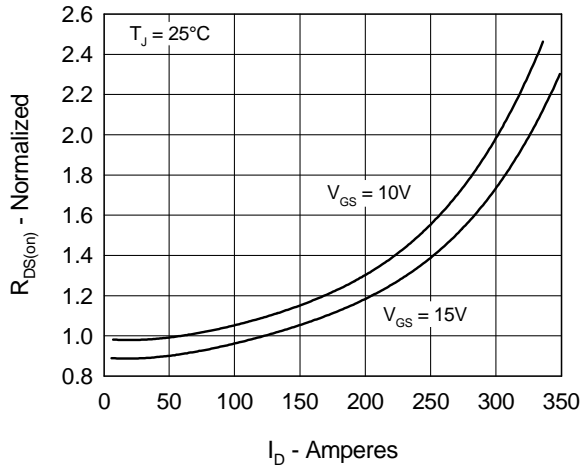


Fig. 4 Temperature Dependence of Drain to Source Resistance

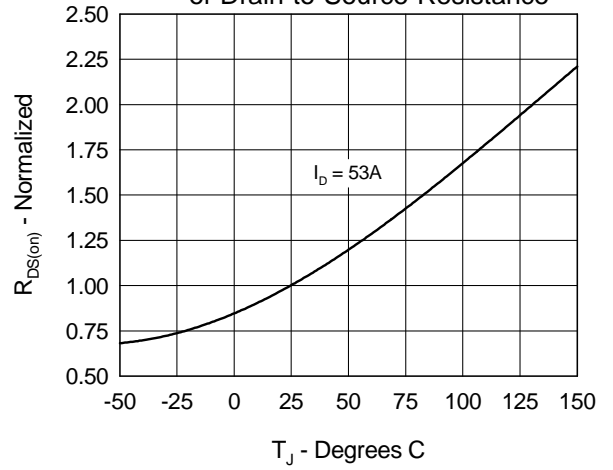


Fig. 5 Drain Current vs. Case Temperature

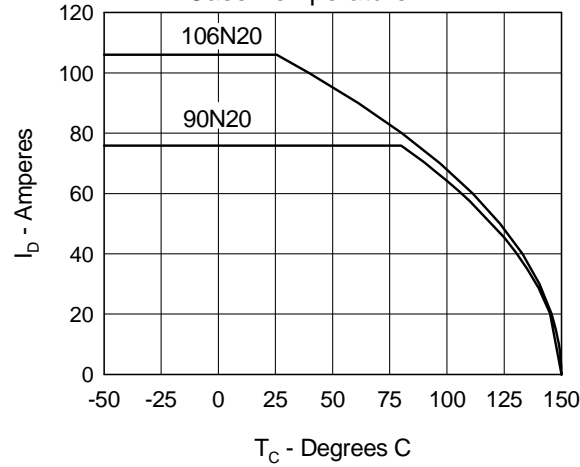


Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage

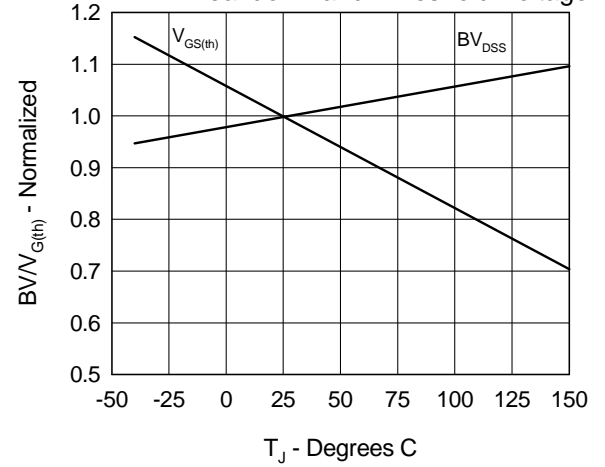


Fig.7 Gate Charge Characteristic Curve

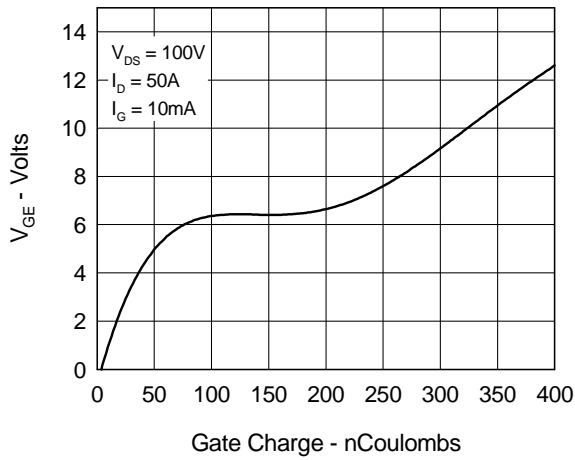


Fig.8 Capacitance Curves

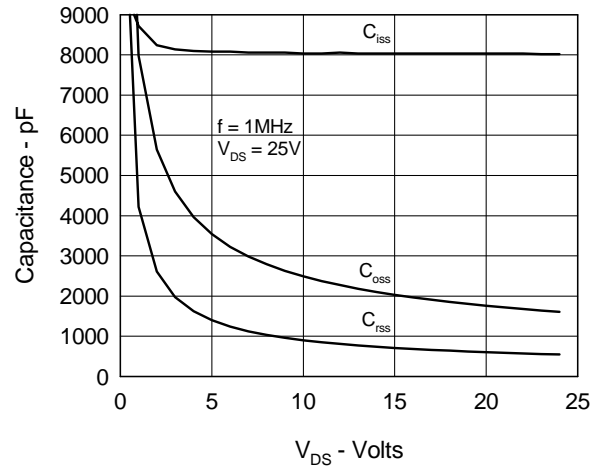


Fig.9 Source Current vs. Source to Drain Voltage

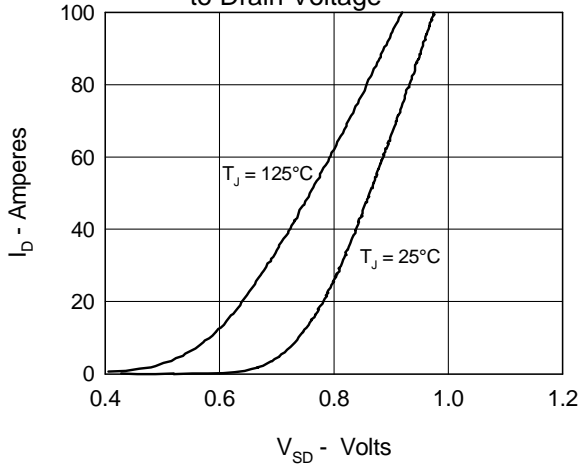
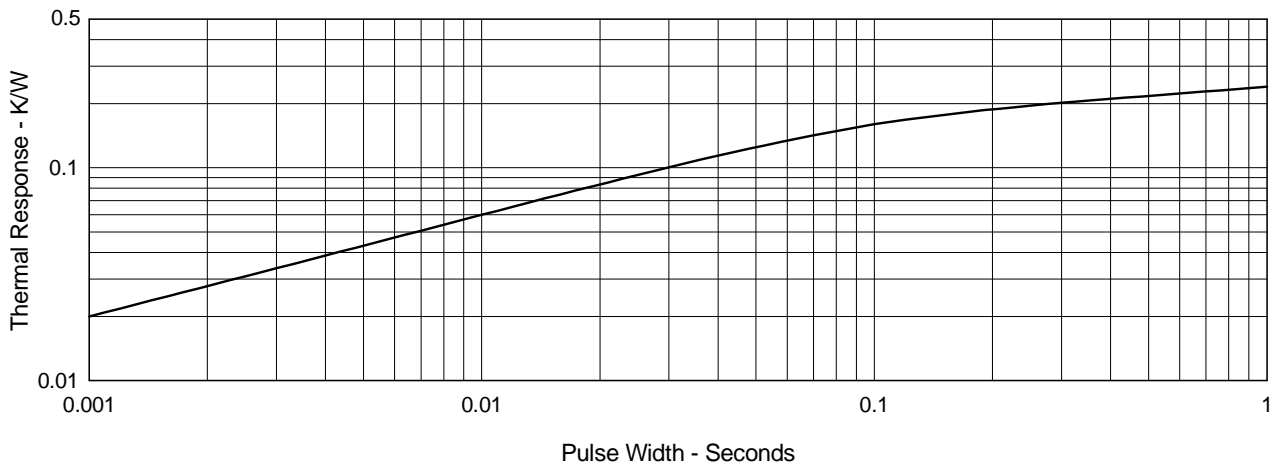


Fig.10 Transient Thermal Impedance





Disclaimer Notice - Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.